AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A Group III nitride semiconductor element comprising

a substrate;

a first nitride semiconductor layer composed of AlN single crystal having a thickness of .005 to .5 μm which is provided on the substrate;

a second nitride semiconductor layer composed of $Al_{x1}Ga_{1-x1}N(0<x1\leq 0.05)$ which is provided on the first nitride semiconductor layer;

~~and~~ a third nitride semiconductor layer composed of $Al_{x2}Ga_{1-x2}N$ $(x1 + 0.02 \leq x2 \leq 0.5)$ which is provided on the second nitride semiconductor layer; and

a fourth nitride semiconductor layer which is provided on the third nitride semiconductor layer, the fourth nitride semiconductor layer including:

an n-type contact layer composed of $Al_aGa_{1-a}N$ $(0 < a < 1)$,

an n-type cladding layer composed of $Al_bGa_{1-b}N$ $(0 < b < 0.4)$ which is provided on the n-type contact layer, and

a light-emitting layer which has a multiple quantum well (MQW) structure including a well layer composed of $Ga_{1-s}In_sN$ $(0 < s < 0.1)$ and a barrier layer composed of $Al_cGa_{1-c}N_c$ $(0 \leq c < 0.3$ and $c < b)$ doped with Si, and is provided on the n-type cladding layer.

2. (original): A Group III nitride semiconductor element according to claim 1, wherein said substrate is selected from a group consisting of sapphire single crystal, Si single crystal, SiC single crystal, AlN single crystal, and GaN single crystal.

3. (previously presented): A Group III nitride semiconductor element according to claim 1, wherein said second nitride semiconductor layer is formed of an island-like structure in which crystals of different heights are arranged so as to be separated from one another.

4. (previously presented): A Group III nitride semiconductor element according to claim 3, wherein the Al content of said second nitride semiconductor layer differs from region to region of the island-like structure.

5. (canceled).

6. (previously presented): A Group III nitride semiconductor element according to claim 1, wherein said second nitride semiconductor layer is composed of $Al_{x1}Ga_{1-x1}N(0<x1\leq 0.02)$.

7. (previously presented): A Group III nitride semiconductor element according to claim 1, wherein said second nitride semiconductor layer has a thickness of 1 to 500 nm.

8. (original): A Group III nitride semiconductor element according to claim 7, wherein said second nitride semiconductor layer has a thickness of 1 to 400 nm.

9. (original): A Group III nitride semiconductor element according to claim 8, wherein said second nitride semiconductor layer has a thickness of 1 to 300 nm.

10. (previously presented): A Group III nitride semiconductor element according to claim 1, wherein said second nitride semiconductor layer is composed of an undoped semiconductor.

11. (currently amended): A Group III nitride semiconductor light-emitting device comprising a Group III nitride semiconductor element according to claim 1, ~~, a~~ wherein:

the fourth nitride semiconductor layer further includes a p-type layer provided on said ~~third nitride semiconductor layer of said semiconductor element, said fourth nitride semiconductor layer including an n-type layer, a light-emitting layer, and a p-type layer, which are successively formed atop said third nitride semiconductor layer in this order;~~ a light-emitting layer,

a negative electrode provided on said n-type contact layer; and

a positive electrode provided on said p-type layer.

12. (original): A light-emitting diode comprising a Group III nitride semiconductor light-emitting device according to claim 11.

13. (original): A laser diode comprising a Group III nitride semiconductor light-emitting device according to claim 11.

14. (previously presented): A semiconductor device comprising a Group III nitride semiconductor element according to claim 1.

15. (canceled).

16. (previously presented): A Group III nitride semiconductor element according to claim 4, wherein the second nitride semiconductor layer has a region having a lower Al content at a position closer to the substrate and a higher Al content at a position farther from the substrate.